8-Bit Serial or Parallel-Input/Serial-Output Shift Register with 3-State Output

High-Performance Silicon-Gate CMOS

The MC74HC589A device consists of an 8-bit storage latch which feeds parallel data to an 8-bit shift register. Data can also be loaded serially (see the Function Table). The shift register output, $Q_{\rm H}$, is a 3-state output, allowing this device to be used in bus-oriented systems.

The HC589A directly interfaces with the SPI serial data port on CMOS MPUs and MCUs.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 526 FETs or 131.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

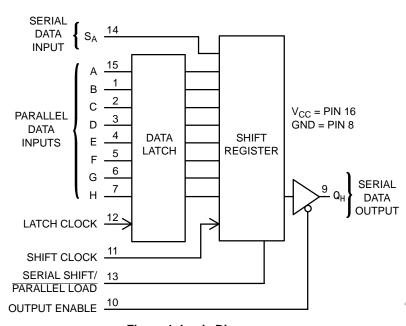


Figure 1. Logic Diagram



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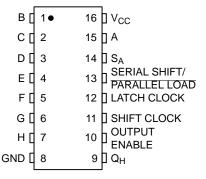
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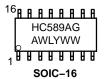


SOIC-16 D SUFFIX CASE 751B TSSOP-16 DT SUFFIX CASE 948F

PIN ASSIGNMENT



MARKING DIAGRAMS





A = Assembly Location WL, L = Wafer Lot

YY, Y = Year WW, W = Work Week G or ■ = Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

MAXIMUM RATINGS

Symbol		Parameter	Value	Unit
V _{CC}	DC Supply Voltage	(Referenced to GND)	-0.5 to +7.0	V
V _{in}	DC Input Voltage	(Referenced to GND)	$-0.5 \le V_{CC} + 0.5$	V
V _{out}	DC Output Voltage	(Referenced to GND)	$-0.5 \le V_{CC} + 0.5$	V
l _{in}	DC Input Current, per Pin		±20	mA
I _{out}	DC Output Current, per Pin		±35	mA
I _{CC}	DC Supply Current, V _{CC} and GND P	ins	±75	mA
I _{GND}	DC Ground Current per Ground Pin		±75	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case	for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance	PDIP SOIC TSSOP	78 112 148	°C/W
P _D	Power Dissipation in Still Air at 85°C	PDIP SOIC TSSOP	750 500 450	mW
MSL	Moisture Sensitivity		Level 1	
F_{R}	Flammability Rating	Oxygen Index: 30% – 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 4000 > 200 > 1000	V
I _{Latchup}	Latchup Performance	Above V _{CC} and Below GND at 85°C (Note 4)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Tested to EIA/JESD22-A114-A.
 Tested to EIA/JESD22-A115-A.
- 3. Tested to JESD22-C101-A.
- 4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage	(Referenced to GND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage	(Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types		-55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 2)	V _{CC} = 2.0 V V _{CC} = 3.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 800 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaran			
Symbol	Parameter	Test Conditions	V	-55°C to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low–Level Input Voltage	V_{out} = 0.1 V or V_{CC} - 0.1 V $ I_{out} \le 20 \mu A$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 2.4 \text{ mA}$ $ I_{out} \le 6.0 \text{ mA}$ $ I_{out} \le 7.8 \text{ mA}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 2.4 \text{ mA}$ $ I_{out} \le 6.0 \text{ mA}$ $ I_{out} \le 7.8 \text{ mA}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μΑ
I _{OZ}	Maximum Three–State Leakage Current	Output in High–Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	6.0	±0.5	±5.0	±10	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

		V _{CC}	Guarar			
Symbol	Parameter	v	–55°C to 25°C	≤ 85°C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 3 and9)	2.0 3.0 4.5 6.0	6.0 15 30 35	4.8 10 24 28	4.0 8.0 20 24	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Latch Clock to Q _H (Figures 2 and 9)	2.0 3.0 4.5 6.0	175 100 40 30	225 110 50 40	275 125 60 50	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Shift Clock to Q _H (Figures 3 and 9)	2.0 3.0 4.5 6.0	160 90 30 25	200 130 40 30	240 160 48 40	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Serial Shift/Parallel Load to Q _H (Figures 5 and 9)	2.0 3.0 4.5 6.0	160 90 30 25	200 130 40 30	240 160 48 40	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Q _H (Figures 4 and 10)	2.0 3.0 4.5 6.0	150 80 27 23	170 100 30 25	200 130 40 30	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Q _H (Figures 4 and 10)	2.0 3.0 4.5 6.0	150 80 27 23	170 100 30 25	200 130 40 30	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 9)	2.0 3.0 4.5 6.0	60 23 12 10	75 27 15 13	90 31 18 15	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State)	-	15	15	15	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (per Package)*	50	pF

^{*}Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

TIMING REQUIREMENTS (Input $t_r = t_f = 6 \text{ ns}$)

		V _{CC}	Guaranteed Limit			
Symbol	Parameter	V	–55°C to 25°C	≤ 85°C	≤ 125°C	Unit
t _{su}	Minimum Setup Time, A–H to Latch Clock (Figure 6)	2.0 3.0 4.5 6.0	100 40 20 17	125 50 25 21	150 60 30 26	ns
t _{su}	Minimum Setup Time, Serial Data Input S _A to Shift Clock (Figure 7)	2.0 3.0 4.5 6.0	100 40 20 17	125 50 25 21	150 60 30 26	ns
t _{su}	Minimum Setup Time, Serial Shift/Parallel Load to Shift Clock (Figure 8)	2.0 3.0 4.5 6.0	100 40 20 17	125 50 25 21	150 60 30 26	ns
t _h	Minimum Hold Time, Latch Clock to A–H (Figure 6)	2.0 3.0 4.5 6.0	25 10 5 5	30 12 6 6	40 15 8 7	ns
t _h	Minimum Hold Time, Shift Clock to Serial Data Input S _A (Figure 7)	2.0 3.0 4.5 6.0	5 5 5 5	5 5 5 5	5 5 5 5	ns
t _w	Minimum Pulse Width, Shift Clock (Figure 3)	2.0 3.0 4.5 6.0	75 40 15 13	95 50 19 16	110 60 23 19	ns
t _w	Minimum Pulse Width, Latch Clock (Figure 2)	2.0 3.0 4.5 6.0	80 40 16 14	100 50 20 17	120 60 24 20	ns
t _w	Minimum Pulse Width, Serial Shift/Parallel Load (Figure 5)	2.0 3.0 4.5 6.0	80 40 16 14	100 50 20 17	120 60 24 20	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 2)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

FUNCTION TABLE

			Input	S			F	Resulting Funct	ion
Operation	Output Enable	Serial Shift/ Parallel Load	Latch Clock	Shift Clock	Serial Input S _A	Parallel Inputs A-H	Data Latch Contents	Shift Register Contents	Output Q _H
Force Output into High Impedance State	Н	Х	Х	Х	Х	Х	Х	Х	Z
Load Parallel Data into Data Latch	L	Н		L, H, ∕_	Х	a-h	a-h	U	U
Transfer Latch Contents to Shift Register	L	L	L, H, ∼	Х	Х	Х	U	$LR_N \!\to \! SR_N$	LR _H
Contents of Input Latch and Shift Register are Unchanged	L	Н	L, H, ∕	L, H, ∼	Х	Х	U	U	U
Load Parallel Data into Data Latch and Shift Register	L	L		Х	Х	a-h	a-h	a–h	h
Shift Serial Data into Shift Register	L	Н	Х	<i></i>	D	Х	*	$SR_A = D,$ $SR_N \rightarrow SR_{N+1}$	$SR_G \to SR_H$
Load Parallel Data in Data Latch and Shift Serial Data into Shift Register	L	Н			D	a-h	a-h	$SR_A = D, \\ SR_N \rightarrow SR_{N+1}$	$SR_G \to SR_H$

LR = latch register contents

SR = shift register contents

a-h = data at parallel data inputs A-H

D = data (L, H) at serial data input S_A

U = remains unchanged

X = don't care

Z = high impedance

* = depends on Latch Clock input

SWITCHING WAVEFORMS

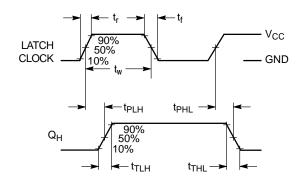


Figure 2. (Serial Shift/Parallel Load = L)

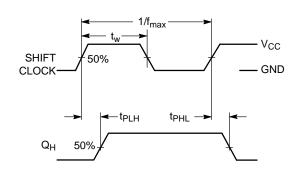


Figure 3. (Serial Shift/Parallel Load = H)

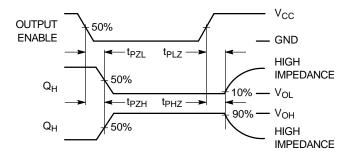


Figure 4.

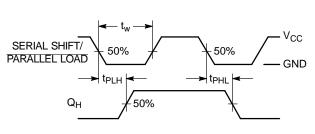


Figure 5.

SWITCHING WAVEFORMS

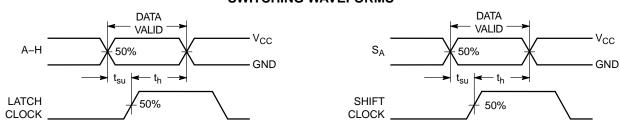


Figure 6.

Figure 7.

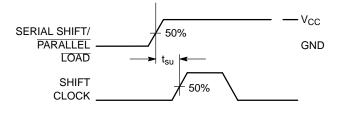
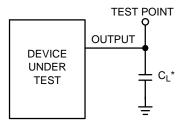


Figure 8.





DEVICE

UNDER

*Includes all probe and jig capacitance.

 $1 k\Omega$

TEST POINT

*Includes all probe and jig capacitance.

Figure 9. Test Circuit

Figure 10. Test Circuit

CONNECT TO V_{CC} WHEN

CONNECT TO GND WHEN

TESTING tpl 7 AND tpzl.

TESTING t_{PHZ} AND t_{PZH}.

PIN DESCRIPTIONS

Data Inputs

A, B, C, D, E, F, G, H (Pins 15, 1, 2, 3, 4, 5, 6, 7)

Parallel data inputs. Data on these inputs are stored in the data latch on the rising edge of the Latch Clock input.

S_A (Pin 14)

Serial data input. Data on this input is shifted into the shift register on the rising edge of the Shift Clock input if Serial Shift/Parallel Load is high. Data on this input is ignored when Serial Shift/Parallel Load is low.

Control Inputs

Serial Shift/Parallel Load (Pin 13)

Shift register mode control. When a high level is applied to this pin, the shift register is allowed to serially shift data. When a low level is applied to this pin, the shift register accepts parallel data from the data latch.

Shift Clock (Pin 11)

Serial shift clock. A low-to-high transition on this input shifts data on the serial data input into the shift register and

data in stage H is shifted out Q_H, being replaced by the data previously stored in stage G.

Latch Clock (Pin 12)

Data latch clock. A low-to-high transition on this input loads the parallel data on inputs A–H into the data latch.

Output Enable (Pin 10)

Active—low output enable A high level applied to this pin forces the Q_H output into the high impedance state. A low level enables the output. This control does not affect the state of the input latch or the shift register.

Output

Q_H (Pin 9)

Serial data output. This pin is the output from the last stage of the shift register. This is a 3–state output.

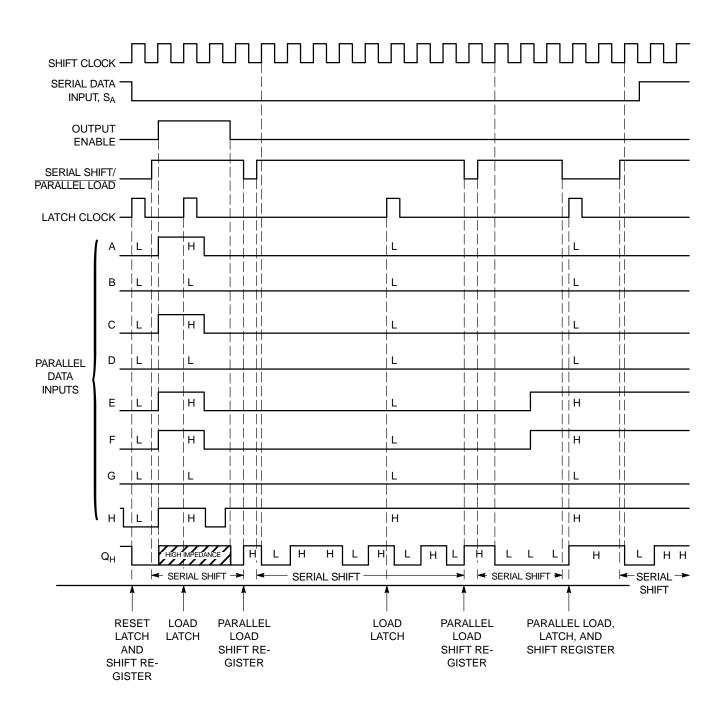
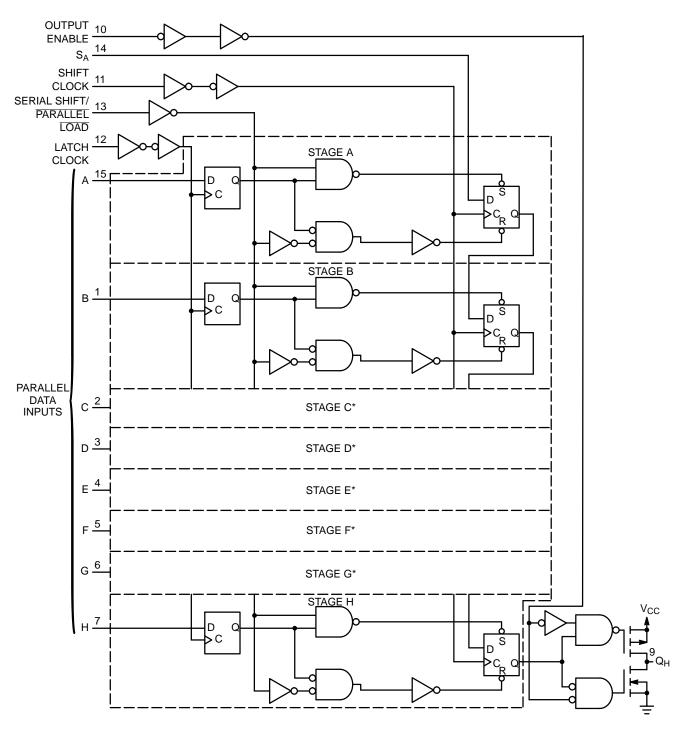


Figure 11. Timing Diagram



*Stages C thru G (not shown in detail) are identical to stages A and B above.

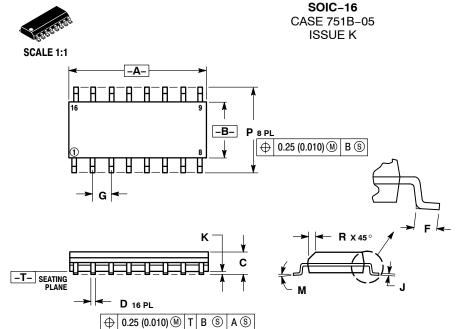
Figure 12. Logic Detail

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC589ADG	SOIC-16 (Pb-Free)	48 Units / Rail
NLV74HC589ADG*	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC589ADR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
NLV74HC589ADR2G*	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74HC589ADTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel
NLV74HC589ADTR2G*	TSSOP-16 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

2. 3.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE	2. 3. 4. 5. 6. 7. 8. 9. 10.	CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION ANODE CATHODE CATHODE ANODE NO CONNECTION ANODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE	2. 3. 4. 5. 6. 7. 8. 9. 10.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #2 COLLECTOR, #3	STYLE 4: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COLLECTOR, #1 COLLECTOR, #2 COLLECTOR, #3 COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 BASE, #4 EMITTER, #4 BASE, #3		
14.	COLLECTOR		NO CONNECTION	14.		14.		SOLDERING	FOOTPRINT
15.	EMITTER		ANODE	15.		15.		8)	(
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	6.4	
STYLE 5: PIN 1. 2. 3. 4. 5. 6. 7. 8.	DRAIN, DYE #1 DRAIN, #1 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4	STYLE 6: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE	STYLE 7: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	SOURCE N-CH COMMON DRAIN (OUTPU' GATE P-CH COMMON DRAIN (OUTPU' COMMON DRAIN (OUTPU' COMMON DRAIN (OUTPU' SOURCE P-CH SOURCE P-CH	T) T) T)	1 0.	6X 1 1 1 1 1 1 1 1 1 1	16
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT	T)			
11.	GATE, #3	11.		11.	COMMON DRAIN (OUTPUT				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT				1.07
13.	GATE, #2	13.	ANODE	13.	GATE N-CH				
14.	SOURCE, #2	14.		14.	COMMON DRAIN (OUTPUT				↓ PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT	T)			+
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH			8	9 + - + + + + + + + + + + + + + + + + +

DOCUMENT NUMBER:	98ASB42566B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED"	' '
DESCRIPTION:	SOIC-16		PAGE 1 OF 1

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☐ 0.10 (0.004)

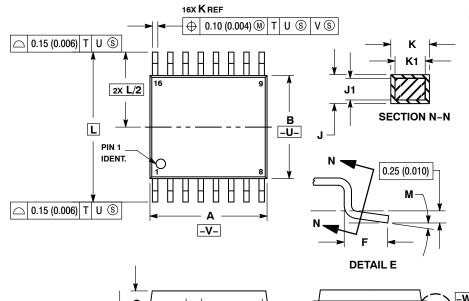
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



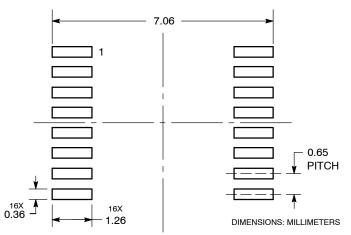
NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
7	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252		
М	٥°	QΟ	٥°	gο	



G



GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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